

AMENDMENTS TO THE CLAIMS

Claims 1-21 (Canceled)

22. (Currently Amended) ~~The high-frequency semiconductor device according to claim 18,~~

A high-frequency semiconductor device comprising:

a semiconductor substrate having a main surface;

a first wiring provided over said main surface of said semiconductor substrate; and

a grounding conductor layer continuously covering a periphery of said first wiring with a first insulator interposed therebetween in a section crossing a direction of extension of said first wiring, wherein

said grounding conductor layer transmits a grounding potential and said grounding conductor layer includes a first portion constituted by only one unit covering an upper surface and two side surfaces of said first wiring and a second portion covering a bottom surface of said first wiring and

wherein said first wiring is electrically connected to said semiconductor substrate through a conductor plug filled in a through hole selectively formed in said grounding conductor layer with a side insulating film interposed therebetween in a part taken in said direction of extension of said first wiring.

Claims 23-24 (Canceled)